

Technical Data Data Sheet N1180, Rev. -

Green Products

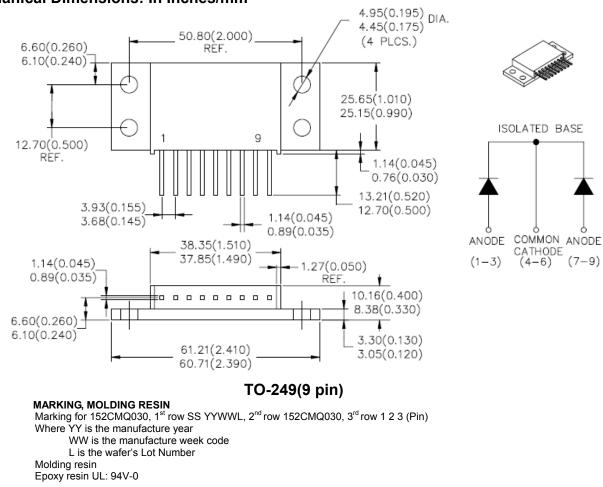
152CMQ030 SCHOTTKY RECTIFIER

Applications:

• Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection Features:

- 150 °C T_J operation
- Isolated heatsink
- Multiple leads per terminal for high frequency, high current PC board mounting
- Low profile, high current package
- Center tap module
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches/mm



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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	VRWM	-	30	V
Max. Average Forward*	I _{F(AV)}	50% duty cycle $@T_c = 85^{\circ}C$, rectangular wave form	150	А
Max. Peak One Cycle Non- Repetitive Surge Current (peg leg)	I _{FSM}	8.3 ms, half Sine pulse	1200	А
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25℃,I _{AS} =15A,L=0.6mH	68	mJ
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T _J max.V _A =1.5 \times V _R typical	15	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 75A, Pulse, T _J = 25 °C @ 150A, Pulse, T _J = 25 °C	0.55 0.69	V
	V_{F2}	@ 75A, Pulse, T _J = 75 °C @ 150A, Pulse, T _J = 75 °C	0.47 0.66	V
Max. Reverse Current (per leg) *	I _{R1}	$@V_R = rated V_R$ T _J = 25 °C	5	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	280	mA
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	3700	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	9.2	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300µs, Duty Cycle <2%

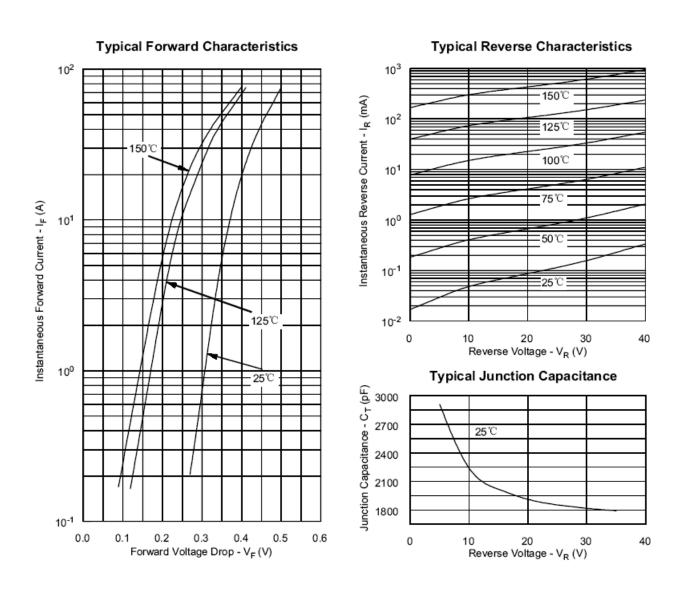
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Max. Junction Temperature	TJ	-	-55 to +150	°C	
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C	
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	1.0	°C/W	
Maximum Thermal Resistance Junction to Case (per package)	$R_{ ext{ heta}JC}$	DC operation	0.5	°C/W	
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.10	°C/W	
Mounting Torque	Тм	-	40(min)	Kg-cm	
			58(max)		
Approximate Weight	wt	-	56	g	
Case Style	TO-249(9 pin)				

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